# N-Channel 20-V (D-S) MOSFET

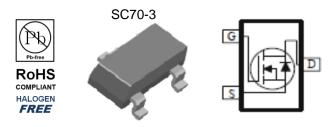
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

#### **Typical Applications:**

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY					
VDS (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$				
20	58 @ V <sub>GS</sub> = 4.5V	2.0			
	82 @ V <sub>GS</sub> = 2.5V	1.7			



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			20	V		
Gate-Source Voltage		V <sub>GS</sub>	±8	V		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	l <sub>D</sub>	2.0	A		
Continuous Drain Current	T <sub>A</sub> =70°C		1.6			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	8			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	0.5	А		
Dower Discinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	0.34	w		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	'D	0.22	۷V		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	375	°C/W		
	Steady State	ιν <sub>θ</sub> ja	430	C/ VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

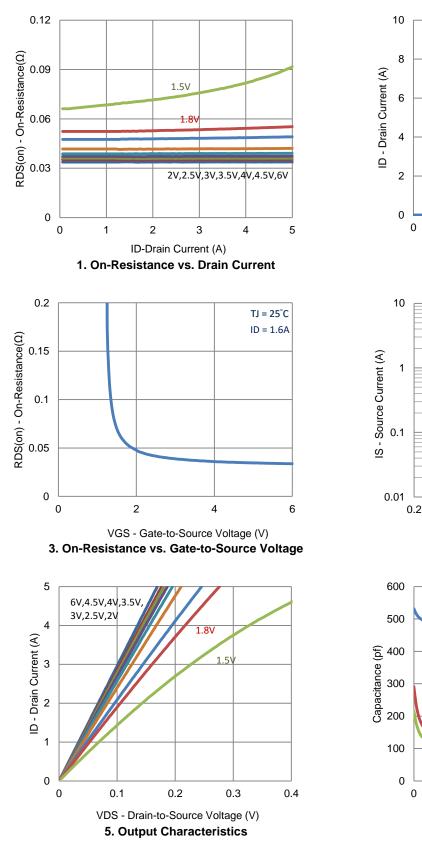
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	uA	
	IDSS	$V_{DS} = 16 \text{ V},  V_{GS} = 0 \text{ V},  \text{T}_{\text{J}} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	3			А	
Drain-Source On-Resistance <sup>a</sup>	r.	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 1.6 \text{ A}$			58	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 1.3 \text{ A}$			82	11152	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 1.6 \text{ A}$		3		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 0.25 \text{ A}, V_{GS} = 0 \text{ V}$		0.58		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg			6			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 1.6 \text{ A}$		0.8		nC	
Gate-Drain Charge	$Q_gd$	1 <u>0</u> – 1.0 A		1.6			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 10 \text{ V}, \text{ R}_{L} = 6.3 \Omega,$		12			
Rise Time	t <sub>r</sub>	$V_{\rm DS} = 10$ V, $N_{\rm L} = 0.3$ $\Omega_{\rm c}$ , $I_{\rm D} = 1.6$ A,		16		200	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		51		ns	
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 4.5 \text{ V},  (V_{\text{GEN}} = 0.32 $		15			
Input Capacitance	C <sub>iss</sub>			433			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		63		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			49			

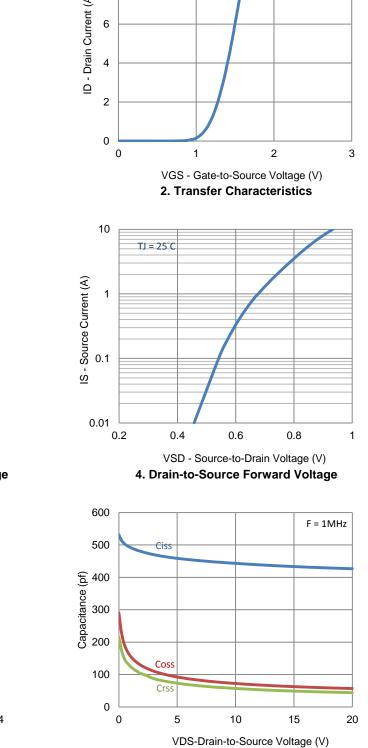
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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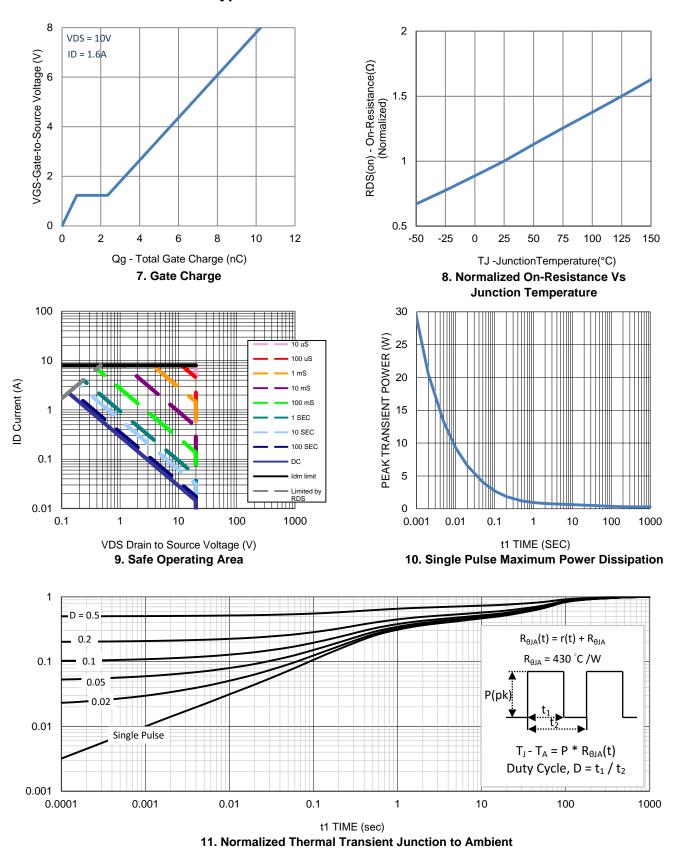






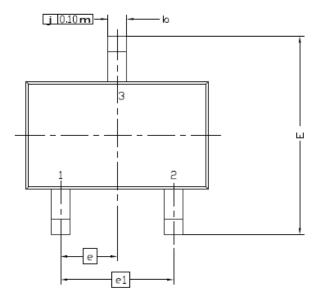
 $TJ = 25^{\circ}C$ 

6. Capacitance



## **Typical Electrical Characteristics**

# Package Information



DIM.	MILLIMETERS			INCHES			
DIM	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0,900	0,95	1,10	0,035	0,037	0.043	
A1	0.00		0.10	0.000		0.004	
A2	0,70	0,90	1.00	0.028	0.035	0.039	
b	0.15	0.22	0.30	0.006	0.016	0.012	
С	0.08	0,127	0,20	0.003	0.005	0.008	
D	210 BSC 0.083 BSC				SC		
E	2.30 BSC			0.091 BSC			
E1	1,30 BSC			0.051 BSC			
6	0.65 BSC			0.026 BSC			
e1	1.30 BSC			0.051 BSC			
L	0,26	0,40	0,46	0,010	0,015	0,018	
L2	0.254BSC			0.010BSC			
R	0.10			0,004			
θ	0°	4°	8°	0°	4°	8°	
θ1		7°N⊡M		7°NDM			

